

ABTEILUNG MATERIALPHYSIK

Veröffentlichungen

[2024](#) | [2023](#) | [2022](#) | [2021](#) | [2020](#) | [2019](#) | [2018](#) | [2017](#) | [2016](#) | [2015](#) | [2014](#) | [2013](#) | [2012](#) | [2011](#) | [2010](#) | [älter als 2010](#)

([\)](#) Liste der Publikationen der Abteilung Materialphysik seit 2010. Die meisten Publikationen sind direkt verlinkt. Wenn Sie Interesse an einer unserer Publikationen haben, sie aber nicht erhalten können, sprechen Sie uns bitte direkt an! ([\)](#)

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- ▶ E. Baron, R. Goldhahn, S. Espinoza, M. Zahradík, M. Rebarz, J. Andreasson, M. Deppe, D.J. As, and M. Feneberg
Time-resolved pump–probe spectroscopic ellipsometry of cubic GaN II: Absorption edge shift with gain and temperature effects
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- ▶ S. Wang, P. Liebing, M. Feneberg, F.M. Sroor, F. Engelhardt, L. Hilmert, S. Busse, E. Kluth, R. Goldhahn, and F.T. Edelmann
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- ▶ E. Kluth, M.W. Fay, C. Parmenter, J.W. Roberts, E. Smith, C.T. Stoppiello, F.C.-P. Massabuau, R. Goldhahn, and M. Feneberg
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Epitaxial synthesis of unintentionally-doped p-type SnO (001) via suboxide molecular beam epitaxy
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Kontakt

Otto-von-Guericke-Universität

Magdeburg

Universitätsplatz 2

39106 Magdeburg

Sekretariat

A. Lidzba

Tel.: 58674

[✉ annette.lidzba@ovgu.de](mailto:annette.lidzba@ovgu.de)

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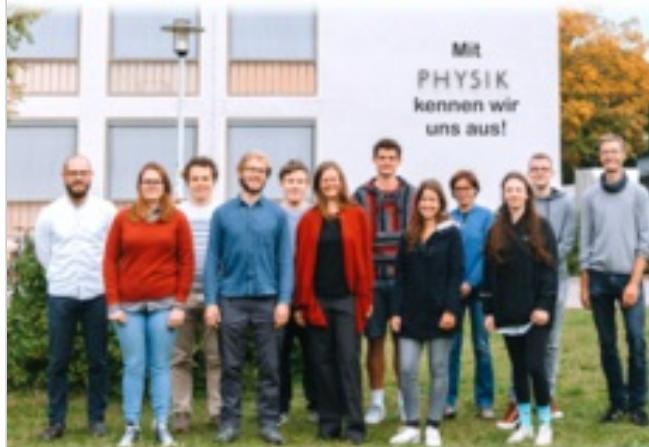


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